# LM8050I, LM8050J

# Amplifier Transistors

## NPN Silicon

ON Semiconductor™

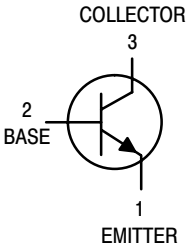
http://onsemi.com

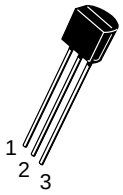
### MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Collector-Emitter Voltage | $V_{CEO}$ | 25 | Vdc |
| Collector-Base Voltage | $V_{CBO}$ | 30 | Vdc |
| Emitter-Base Voltage | $V_{EBO}$ | 6.0 | Vdc |
| Collector Current – Continuous | $I_C$ | 800 | mAdc |
| Total Device Dissipation<br>@ $T_A$ = 25°C<br>Derate above 25°C | $P_D$ | <br>625<br>5.0 | <br>mW<br>mW/°C |
| Total Device Dissipation<br>@ $T_C$ = 25°C<br>Derate above 25°C | $P_D$ | <br>1.5<br>12 | <br>Watts<br>mW/°C |
| Operating and Storage Junction Temperature Range | $T_J$, $T_{stg}$ | –55 to +150 | °C |

### THERMAL CHARACTERISTICS

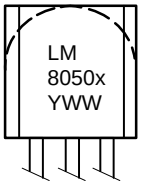
| Characteristic | Symbol | Max | Unit |
|---|---|---|---|
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 200 | °C/W |
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 83.3 | °C/W |




**TO–92**
**CASE 29**
**STYLE 1**

### MARKING DIAGRAMS




LM8050x = Specific Device Code
x = I or J
Y = Year
WW = Work Week

### ORDERING INFORMATION

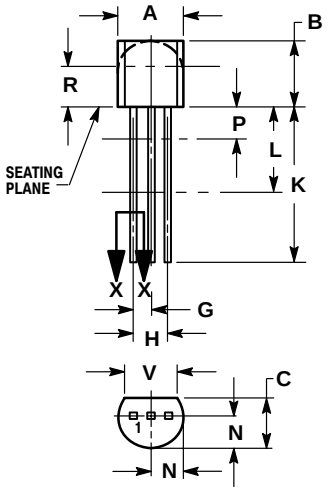
| Device | Package | Shipping |
|---|---|---|
| LM8050I | TO–92 | 5000 Units/Box |
| LM8050J | TO–92 | 5000 Units/Box |

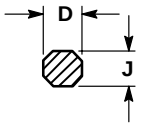
**ELECTRICAL CHARACTERISTICS** ($T_A$ = 25°C unless otherwise noted)

| Characteristic | | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Collector–Emitter Breakdown Voltage ($I_C$ = 1.0 mAdc, $I_B$ = 0) | | $V_{(BR)CEO}$ | 25 | – | – | Vdc |
| Collector–Base Breakdown Voltage ($I_C$ = 0.5 mAdc, $I_E$ = 0) | | $V_{(BR)CBO}$ | 30 | – | – | Vdc |
| Emitter–Base Breakdown Voltage ($I_E$ = 0.1 mAdc, $I_C$ = 0) | | $V_{(BR)EBO}$ | 6.0 | – | – | Vdc |
| Collector Cutoff Current ($V_{CB}$ = 15 Vdc, $I_E$ = 0) | | $I_{CBO}$ | – | – | 50 | nAdc |
| **ON CHARACTERISTICS** | | | | | | |
| DC Current Gain | | $h_{FE}$ | | | | – |
| ($I_C$ = 50 mAdc, $V_{CE}$ = 1.0 Vdc) | LM8050I | | 100 | – | 200 | |
| | LM8050J | | 150 | – | 300 | |
| ($I_C$ = 350 mAdc, $V_{CE}$ = 1.0 Vdc) | | | 60 | – | – | |
| Collector–Emitter Saturation Voltage ($I_C$ = 500 mAdc, $I_B$ = 50 mAdc) | | $V_{CE(sat)}$ | – | – | 0.5 | Vdc |
| Base–Emitter Saturation Voltage ($I_C$ = 500 mAdc, $I_B$ = 50 mAdc) | | $V_{BE(sat)}$ | – | – | 1.2 | Vdc |

## PACKAGE DIMENSIONS

**TO–92 (TO–226)**
CASE 29–11
ISSUE AL




SECTION X–X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| | INCHES | | MILLIMETERS | |
|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX |
| A | 0.175 | 0.205 | 4.45 | 5.20 |
| B | 0.170 | 0.210 | 4.32 | 5.33 |
| C | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.021 | 0.407 | 0.533 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| H | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | --- | 12.70 | --- |
| L | 0.250 | --- | 6.35 | --- |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| P | --- | 0.100 | --- | 2.54 |
| R | 0.115 | --- | 2.93 | --- |
| V | 0.135 | --- | 3.43 | --- |

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

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